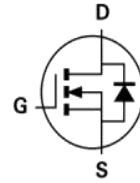


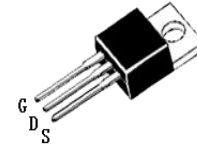
MAIN CHARACTERISTICS

I_D	110A
V_{DSS}	55V
$R_{DS(on)-typ}$ (@ $V_{GS}=10V, I_D = 55 A$)	6.5m Ω



FEATURES

- Fast Switching
- Low ON Resistance
- Low Gate Charge
- 100% Single Pulse avalanche energy Test



TO-220AB

APPLICATIONS

- Power switch circuit of adaptor and charger.

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275°C maximum, 10s per JESD 22-B106

Product specification classification

Part Number	Package	Mode Name	Pack
LX3205A1	TO-220AB	LX3205A	Tube

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	55	V
Gate-Source Voltage	V_{GS}	±20	V
Continue Drain Current	I_D	110	A
Pulsed Drain Current (Note1)	I_{DM}	390	A
Power Dissipation	P_D	200	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	20	mJ
Operating Temperature Range	T_J	175	°C
Storage Temperature Range	T_{STG}	-55 to +175	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.75	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62	°C/W

Electrical Characteristics at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	BV_{DSS}	55	-	-	V
Drain-Source Leakage Current	$V_{DS} = 55V, V_{GS} = 0 V$	I_{DSS}	-	-	25	μA
Gate Leakage Current	$V_{GS} = \pm 20 V, V_{DS} = 0 V$	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	$V_{GS(th)}$	2	-	4	V
Drain-Source On-State Resistance	$V_{GS} = 10 V, I_D = 1 A$	$R_{DS(on)}$	-	6.5	9	m Ω
Drain-Source On-State Resistance	$V_{GS} = 10 V, I_D = 30 A$	$R_{DS(on)}$	-	6.8	8	m Ω
Drain-Source On-State Resistance	$V_{GS} = 10 V, I_D = 55 A$	$R_{DS(on)}$	-	6.5	7	m Ω
Forward Transconductance	$V_{DS} = 50 V, I_D = 35 A$	g_{fs}	44	-	-	S
Input Capacitance	$V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz$	C_{iss}	-	3247	-	pF
Output Capacitance		C_{oss}	-	781	-	pF
Reverse Transfer Capacitance		C_{rss}	-	211	-	pF
Turn-on Delay Time(Note2)	$I_D = 55 A, V_{DD} = 25 V, R_G = 4.5 \Omega, V_{GS} = 10 V$	$t_{d(ON)}$	-	14	-	ns
Rise Time(Note2)		t_r	-	101	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	50	-	ns
Fall Time(Note2)		t_f	-	65	-	ns
Total Gate Charge(Note2)	$I_D = 55 A, V_{DD} = 40 V, V_{GS} = 10 V$	Q_G	-	-	146	nC
Gate to Source Charge(Note2)		Q_{GS}	-	-	35	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	-	54	nC

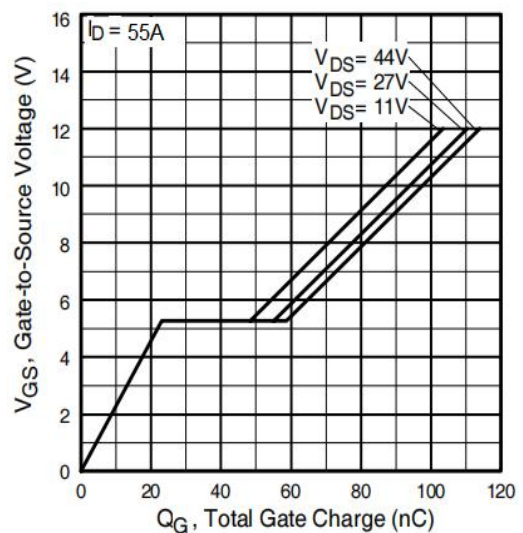
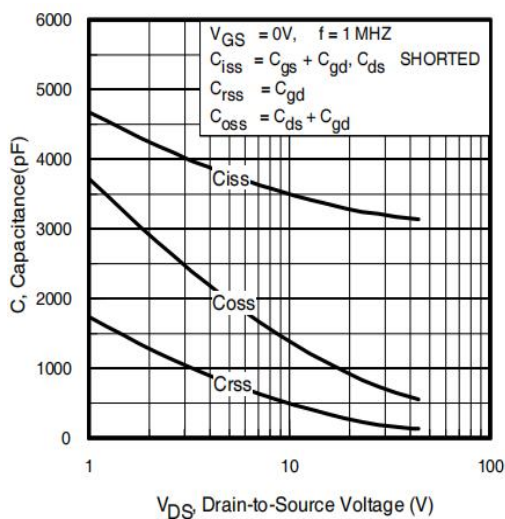
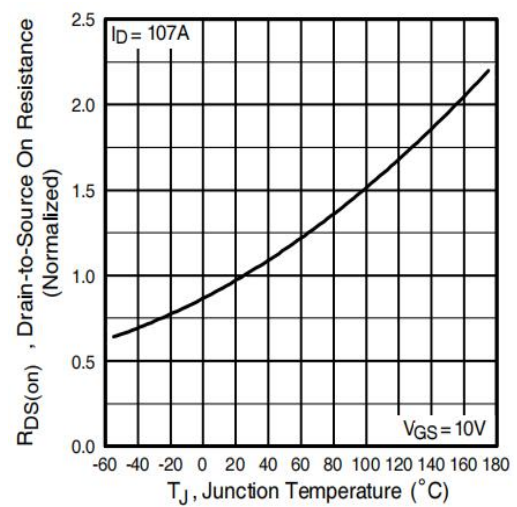
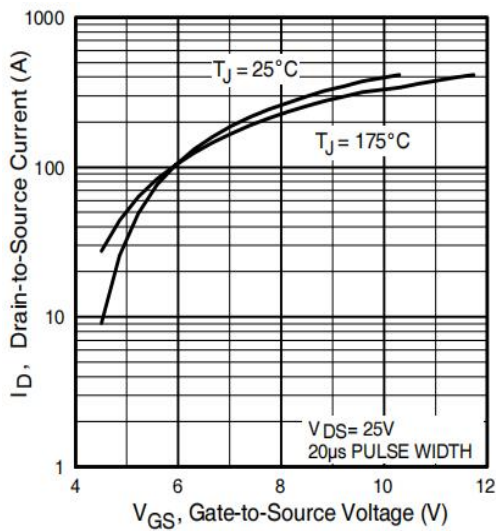
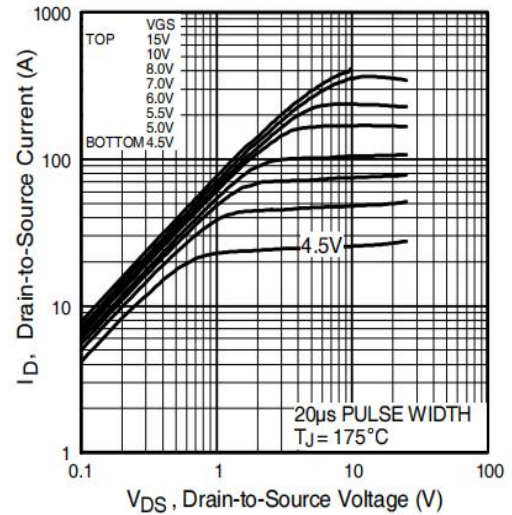
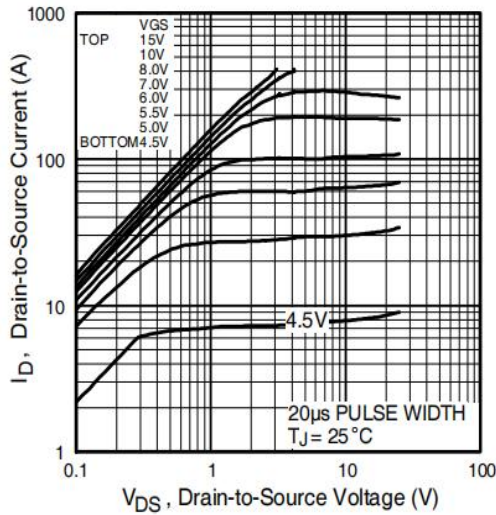
Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Characteristics	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	110	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	390	A
Drain-Source Diode Forward Voltage	$I_{SD} = 25A$	V_{SD}	-	-	1	V
Reverse Recovery Time(Note2)	$I_F = 55A, dl_F / dt = 100 A/\mu s$	t_{rr}	-	-	104	ns
Reverse Recovery Charge(Note2)		Q_{rr}	-	-	215	nC

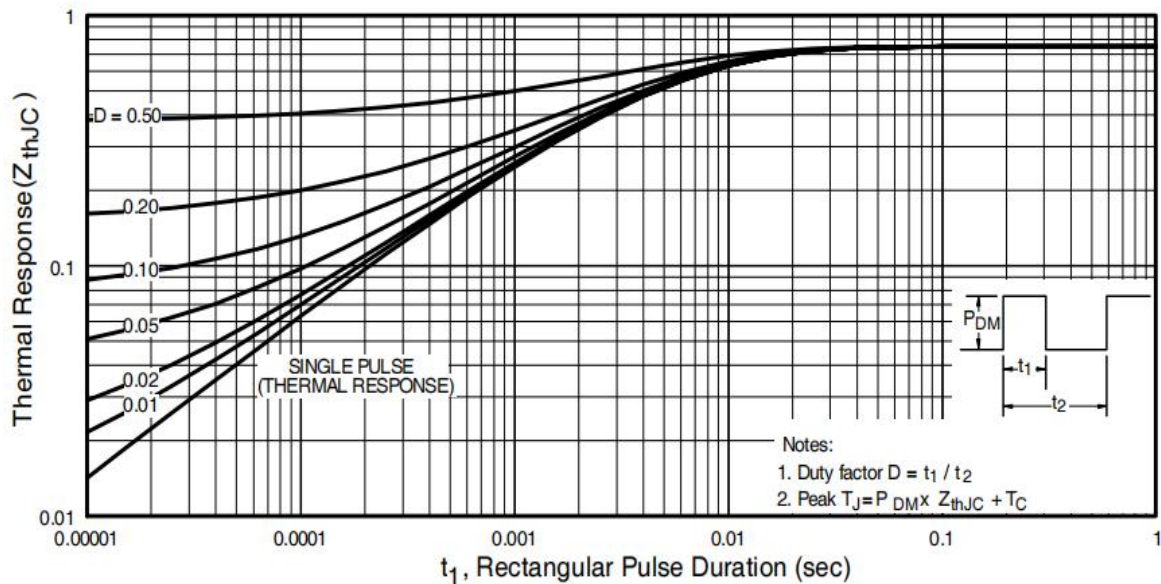
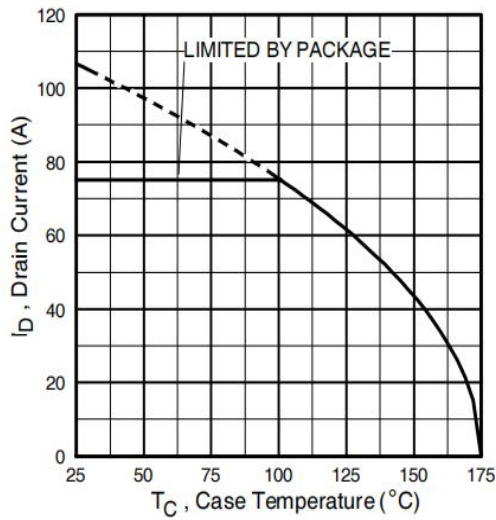
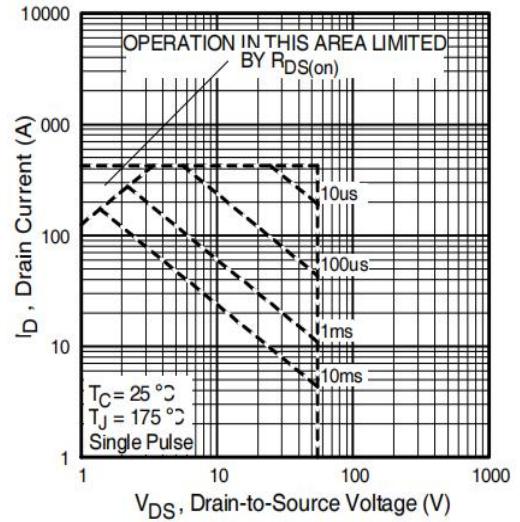
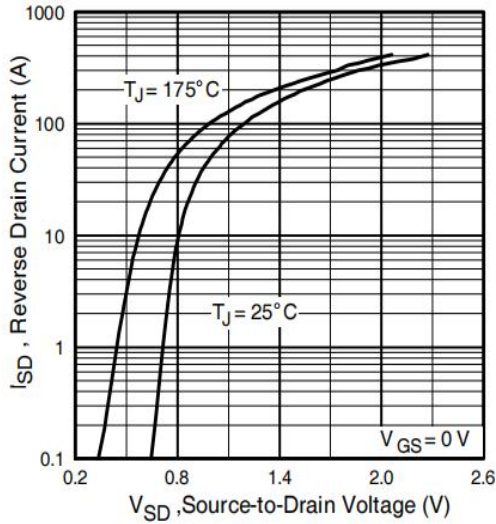
Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

RATINGS AND CHARACTERISTIC CURVES

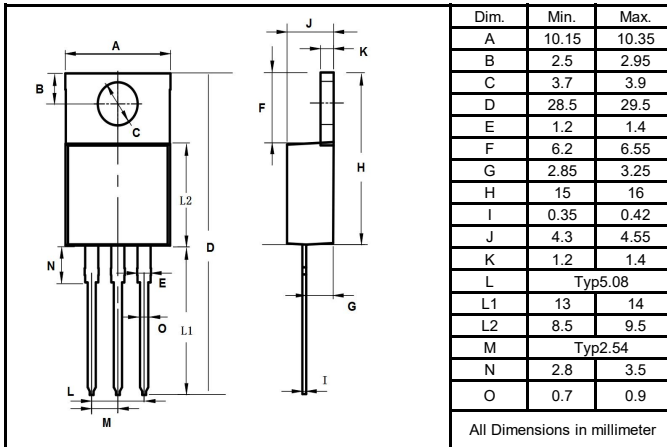


RATINGS AND CHARACTERISTIC CURVES

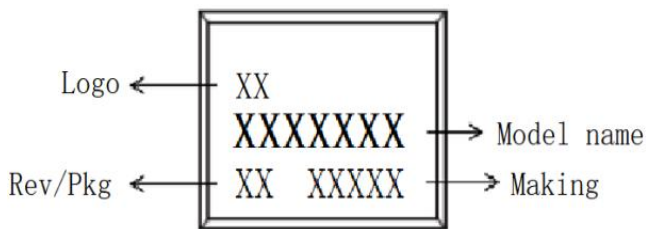


Package Outline Dimensions millimeters

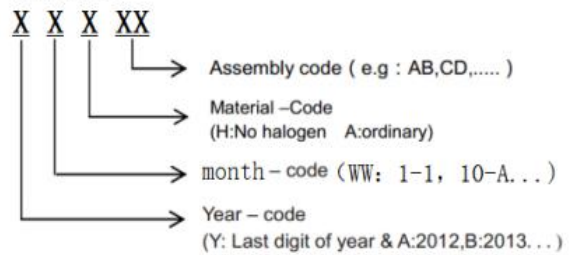
TO-220AB



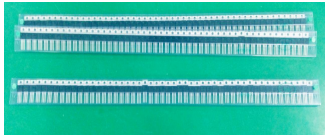
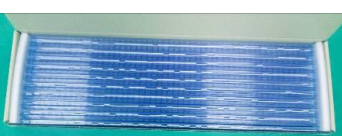
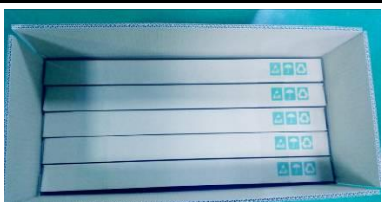
Marking on the body



MAKING:



packing instruction

PKG	最小包装	内盒	外箱
TO-220AB			
	50PCS/管	1000pcs/盒	5000pcs/箱

Notice

All product,product specifications and data are subject to change without notice to improve.The right to explain is owned by LINGXUN electronics

company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying poer exceeding normal rated

poer; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.